1-of-8 Decoder/ Demultiplexer

High-Performance Silicon-Gate CMOS

The MC74HC238A is identical in pinout to the LS238. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC238A decodes a three-bit Address to one-of-eight active-high outputs. This device features three Chip Select inputs, two active-low and one active-high to facilitate the demultiplexing, cascading, and chip-selecting functions. The demultiplexing function is accomplished by using the Address inputs to select the desired device output; one of the Chip Selects is used as a data input while the other Chip Selects are held in their active states.

Features

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2.0 V to 6.0 V
- Low Input Current: 1.0 µA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 100 FETs or 29 Equivalent Gates
- These are Pb-Free Devices*



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ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



Figure 2. Logic Diagram

ORDERING INFORMATION

Device	Package	Shipping [†]
MC74HC238ANG	PDIP-16 (Pb-Free)	500 Units / Rail
MC74HC238ADG	SOIC-16 (Pb-Free)	48 Units / Rail
MC74HC238ADR2G	SOIC-16 (Pb-Free)	2500 Tape & Reel
MC74HC238ADTR2G	TSSOP-16*	2500 Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
 *This package is inherently Pb-Free.

TRUTH TABLE

	Inputs			Outputs									
CS3	CS2	CS1	A0	A1	A2	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
Н	Х	Х	Х	Х	Х	L	L	L	L	L	L	L	L
Х	Н	Х	Х	Х	Х	L	L	L	L	L	L	L	L
Х	Х	L	х	Х	Х	L	L	L	L	L	L	L	L
L	L	н	L	L	L	Н	L	L	L	L	L	L	L
L	L	н	Н	L	L	L	н	L	L	L	L	L	L
L	L	н	L	Н	L	L	L	Н	L	L	L	L	L
L	L	н	Н	Н	L	L	L	L	Н	L	L	L	L
L	L	н	L	L	Н	L	L	L	L	Н	L	L	L
L	L	н	Н	L	Н	L	L	L	L	L	Н	L	L
L	L	н	L	Н	Н	L	L	L	L	L	L	Н	L
L	L	Н	Н	Н	Н	L	L	L	L	L	L	L	Н

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	– 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	$-$ 0.5 to V_{CC} + 0.5	V
V _{out}	DC Output Voltage (Referenced to GND)	$-$ 0.5 to V_{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	± 20	mA
I _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 50	mA
P _D	Power Dissipation in Still Air, Plastic DIP† SOIC Package† TSSOP Package†	750 500 450	mW
T _{stg}	Storage Temperature	– 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP, SOIC or TSSOP Package)	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and Vout should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

†Derating -Plastic DIP: - 10 mW/°C from 65° to 125°C

SOIC Package: -7 mW/°C from 65° to 125°C TSSOP Package: -6.1 .W/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
$V_{\text{in}}, V_{\text{out}}$	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 2.0 \text{ V}$ (Figure 2) $V_{CC} = 4.5 \text{ V}$ $V_{CC} = 6.0 \text{ V}$	0 0 0	1000 500 400	ns

			V _{CC}	Guaranteed Limit			
Symbol	Parameter	Test Conditions	v	−55°C to 25°C	≤ 85°C	≤ 125°C	Unit
V _{IH}	Minimum High–Level Input Voltage	$\begin{array}{l} V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V} \\ I_{out} \leq 20 \ \mu\text{A} \end{array}$	2.0 3.0 4.5 6.0	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	1.5 2.1 3.15 4.2	V
V _{IL}	Maximum Low–Level Input Voltage	$\begin{array}{l} V_{out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V} \\ I_{out} \leq 20 \ \mu\text{A} \end{array}$	2.0 3.0 4.5 6.0	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	0.5 0.9 1.35 1.8	V
V _{OH}	Minimum High–Level Output Voltage	$ \begin{aligned} V_{in} &= V_{IH} \text{ or } V_{IL} \\ I_{out} &\leq 20 \ \mu A \end{aligned} $	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$ \begin{array}{l l} V_{in} = V_{IH} \text{ or } V_{IL} \ \left I_{out} \right \leq 2.4 \text{ mA} \\ \left I_{out} \right \leq 4.0 \text{ mA} \\ \left I_{out} \right \leq 5.2 \text{ mA} \end{array} $	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

V _{OL}	Maximum Low-Level Output Voltage	$ \begin{aligned} V_{in} &= V_{IH} \text{ or } V_{IL} \\ I_{out} &\leq 20 \ \mu A \end{aligned} $	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$\label{eq:Vin} \begin{array}{ c c } V_{in} = V_{IH} \text{ or } V_{IL} & I_{out} \leq 2.4 \text{ mA} \\ & I_{out} \leq 4.0 \text{ mA} \\ & I_{out} \leq 5.2 \text{ mA} \end{array}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l _{in}	Maximum Input Leakage Current	V _{in} = V _{CC} or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
ICC	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC} \text{ or } GND$ $I_{out} = 0 \ \mu A$	6.0	4	40	160	μΑ

AC ELECTRICAL CHARACTERISTICS (CL = 50 pF, Input $t_r = t_f = 6.0 \text{ ns}$)

		V _{cc}	Guara			
Symbol	Parameter		–55°C to 25°C	≤ 85 °C	≤ 125°C	Unit
t _{PLH} ,	Maximum Propagation Delay, Input A to Output Y	2.0	135	170	205	ns
t _{PHL}	(Figures 3 and 6)	3.0	90	125	165	
		4.5	27	34	41	
		6.0	23	29	35	
t _{PLH} ,	Maximum Propagation Delay, CS1 to Output Y	2.0	110	140	165	ns
t _{PHL}	(Figures 4 and 6)	3.0	85	100	125	
		4.5	22	28	33	
		6.0	19	24	28	
t _{PLH} ,	Maximum Propagation Delay, CS2 or CS3 to Output Y	2.0	120	150	180	ns
t _{PHL}	(Figures 5 and 6)	3.0	90	120	150	
		4.5	24	30	36	
		6.0	20	26	31	
t _{TLH} ,	Maximum Output Transition Time, Any Output	2.0	75	95	110	ns
t _{THL}	(Figures 4 and 6)	3.0	30	40	55	
=	,	4.5	15	19	22	
		6.0	13	16	19	
C _{in}	Maximum Input Capacitance	-	10	10	10	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Per Package)*	55	pF

* Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$.

SWITCHING WAVEFORMS



PIN DESCRIPTIONS

ADDRESS INPUTS

A0, A1, A2 (Pins 1, 2, 3)

Address inputs. These inputs, when the chip is selected, determine which of the eight outputs is active-low.

CONTROL INPUTS CS1, CS2, CS3 (Pins 6, 4, 5)

Chip select inputs. For CS1 at a high level and CS2, CS3 at a low level, the chip is selected and the outputs follow the

Address inputs. For any other combination of CS1, CS2, and CS3, the outputs are at a logic low.

OUTPUTS

Y0 - Y7 (Pins 15, 14, 13, 12, 11, 10, 9, 7)

Active-high Decoded outputs. These outputs assume a high level when addressed and the chip is selected. These outputs remain low when not addressed or the chip is not selected.

EXPANDED LOGIC DIAGRAM



PACKAGE DIMENSIONS

PDIP-16 **N SUFFIX** CASE 648-08 ISSUE T



NOTES:

- 1. DIMENSIONING AND TOLERANCING PER
- DIMENSIONING AND TOLERANCING F ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL. DIMENSION B DOES NOT INCLUDE MOLD FLASH. 2.
- З.
- 4
- 5. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIM	ETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.70	1.02	1.77
G	0.100 BSC		2.54	BSC
н	0.050 BSC		1.27	BSC
J	0.008	0.015	0.21	0.38
κ	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
М	0 °	10 °	0 °	10 °
S	0.020	0.040	0.51	1.01

SOIC-16 **D SUFFIX** CASE 751B-05 ISSUE J



NOTES:

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION. 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) DED 0005

- PER SIDE. 5. DIMENSION D DOES NOT INCLUDE DAMBAR
- PROTRUSION & DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	9.80	10.00	0.386	0.393	
В	3.80	4.00	0.150	0.157	
C	1.35	1.75	0.054	0.068	
D	0.35	0.49	0.014	0.019	
F	0.40	1.25	0.016	0.049	
G	1.27	BSC	0.050 BSC		
J	0.19	0.25	0.008	0.009	
K	0.10	0.25	0.004	0.009	
М	0 °	7°	0 °	7°	
Р	5.80	6.20	0.229	0.244	
R	0.25	0.50	0.010	0.019	

PACKAGE DIMENSIONS





NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER. 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH. PROTRUSIONS OR GATE BURRS.
- MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE. 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION.
- INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION

6. TERMINAL NUMBERS ARE SHOWN FOR

REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

	MILLIN	IETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	4.90	5.10	0.193	0.200	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
н	0.18	0.28	0.007	0.011	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
к	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40		0.252	2 BSC	
Μ	0 °	8 °	0 °	8 °	

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